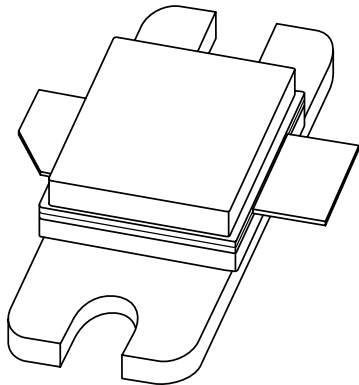


DATA SHEET



BLS3135-50 Microwave power transistor

Product specification
Supersedes data of 1999 Aug 16

2003 Apr 15

Microwave power transistor

BLS3135-50

FEATURES

- Suitable for short and medium pulse applications
- Internal input and output matching networks for an easy circuit design
- Emitter ballasting resistors improve ruggedness
- Gold metallization ensures excellent reliability
- Interdigitated emitter-base structure provides high emitter efficiency
- Multicell geometry improves power sharing and reduces thermal resistance.

APPLICATIONS

- Common base class-C pulsed power amplifiers for radar applications in the 3.1 to 3.5 GHz band.

DESCRIPTION

NPN silicon planar epitaxial microwave power transistor in a 2-lead rectangular flange package with a ceramic cap (SOT422A) with the common base connected to the flange.

PINNING - SOT422A

PIN	DESCRIPTION
1	collector
2	emitter
3	base; connected to flange

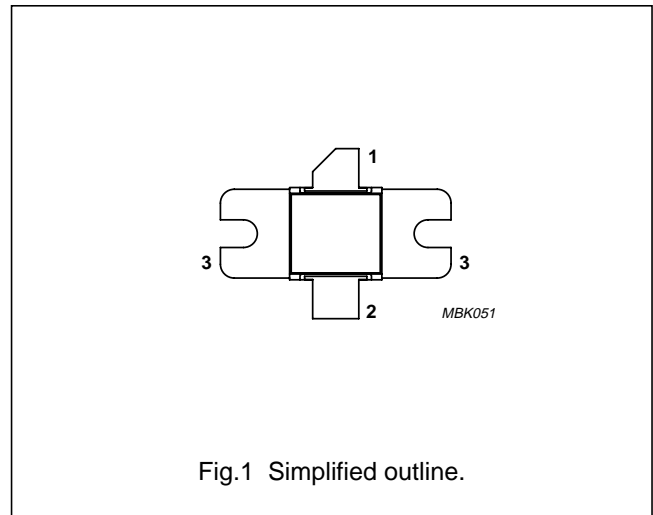


Fig.1 Simplified outline.

QUICK REFERENCE DATA

RF performance at $T_h = 25\text{ }^\circ\text{C}$ in a common base class-C test circuit.

MODE OF OPERATION	f (GHz)	V_{CB} (V)	P_L (W)	G_p (dB)	η_c (%)
Pulsed, class-C	3.1 to 3.5	40	50	typ. 8	typ. 40

WARNING

Product and environmental safety - toxic materials

This product contains beryllium oxide. The product is entirely safe provided that the BeO disc is not damaged. All persons who handle, use or dispose of this product should be aware of its nature and of the necessary safety precautions. After use, dispose of as chemical or special waste according to the regulations applying at the location of the user. It must never be thrown out with the general or domestic waste.

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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	75	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	75	V
V_{EBO}	emitter-base voltage	open collector	–	2	V
I_{CM}	peak collector current	$t_p \leq 100 \mu\text{s}$; $\delta \leq 10\%$	–	6	A
P_{tot}	total power dissipation	$t_p = 100 \mu\text{s}$; $\delta = 10\%$; $T_{mb} = 25 \text{ }^\circ\text{C}$	–	80	W
T_{stg}	storage temperature		–65	+200	$^\circ\text{C}$
T_j	operating junction temperature		–	200	$^\circ\text{C}$
T_{sld}	soldering temperature	up to 0.2 mm from ceramic cap; $t \leq 10 \text{ s}$	–	235	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$Z_{th\ j-h}$	thermal impedance from junction to heatsink	$t_p = 100 \mu\text{s}$; $\delta = 10\%$; note 1	0.71	K/W
		$t_p = 300 \mu\text{s}$; $\delta = 10\%$; note 1	0.99	K/W

Note

1. Equivalent thermal impedance under pulsed microwave operating conditions. Measured with IR-scan with 20 μm spot size at hotspot.

CHARACTERISTICS

 $T_j = 25 \text{ }^\circ\text{C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 15 \text{ mA}$; open emitter	75	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$I_C = 15 \text{ mA}$; $V_{BE} = 0$	75	–	V
I_{CBO}	collector leakage current	$V_{CB} = 40 \text{ V}$; $I_E = 0$	–	1.5	mA
I_{CES}	collector leakage current	$V_{CE} = 40 \text{ V}$; $V_{BE} = 0$	–	3	mA
I_{EBO}	emitter leakage current	$V_{EB} = 1.5 \text{ V}$; $I_C = 0$	–	0.3	mA
h_{FE}	DC current gain	$V_{CB} = 5 \text{ V}$; $I_C = 1.5 \text{ A}$	40	–	

APPLICATION INFORMATION

RF performance at $T_h = 25 \text{ }^\circ\text{C}$ in a common-base test circuit.

MODE OF OPERATION	f (GHz)	V_{CE} (V)	P_L (W)	G_p (dB)	η_c (%)
Class-C; $t_p = 100 \mu\text{s}$; $\delta = 10\%$	3.1 to 3.5	40	≥ 50 typ. 55	≥ 7 typ. 8	≥ 35 typ. 40

Microwave power transistor

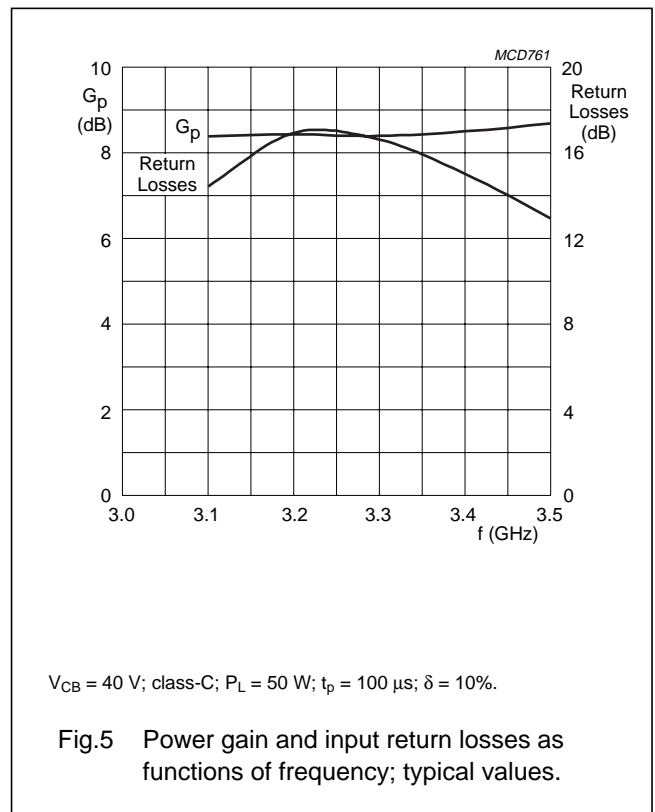
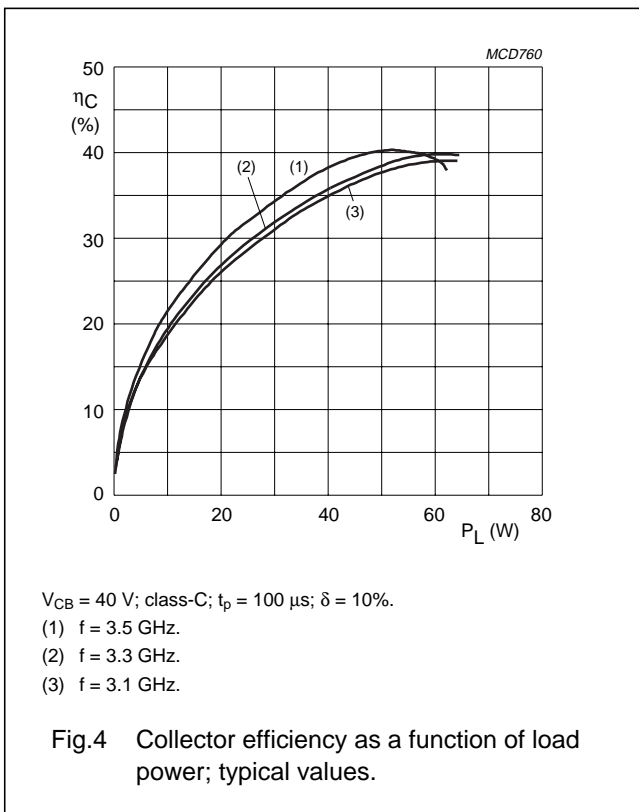
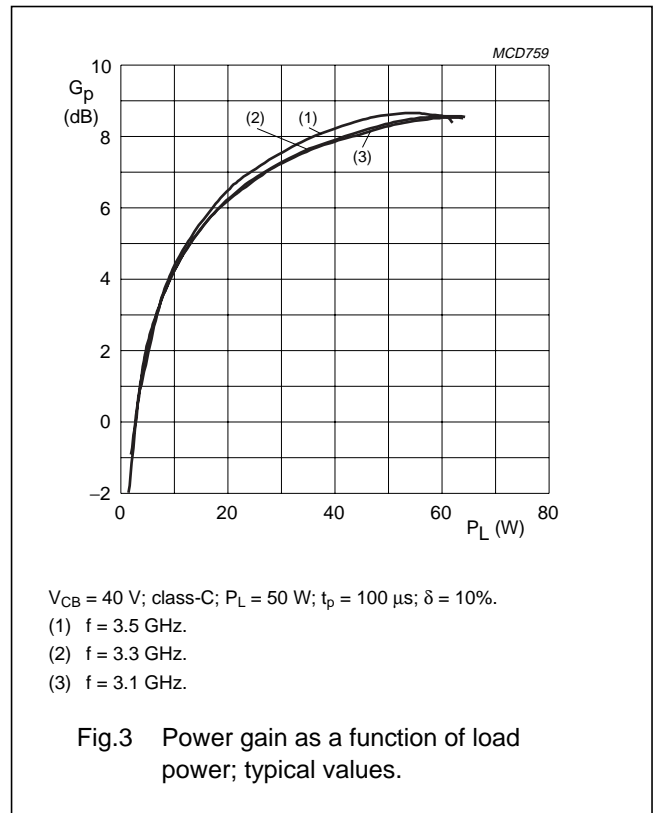
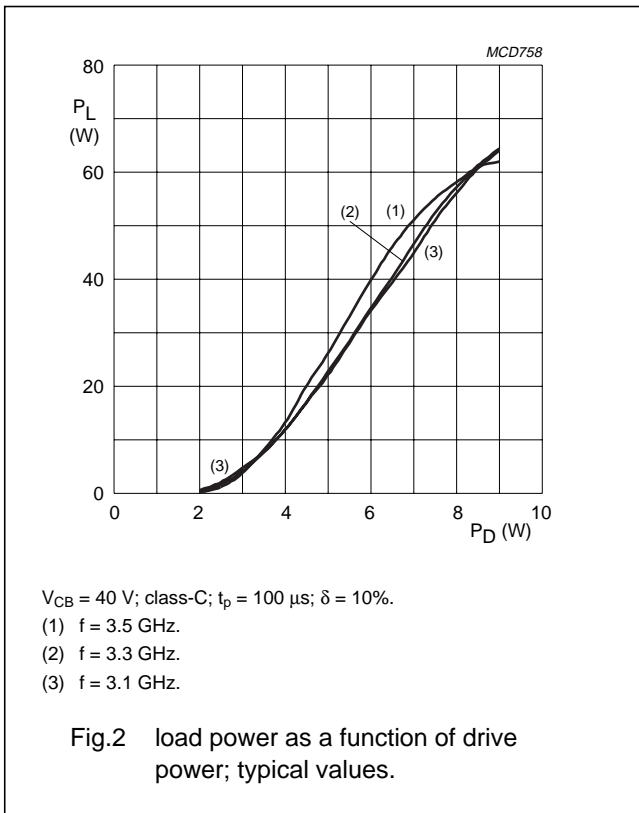
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Typical impedance

FREQUENCY (GHZ)	Z_S (Ω)	Z_L (Ω)
3.1	23.5 - j 5.6	7.8 - j 3.7
3.2	23.6 - j 4.3	7.3 - j 4.1
3.3	23.8 - j 2.9	6.6 - j 4.3
3.4	24.3 - j 1.6	5.8 - j 4.2
3.5	24.9 - j 0.3	5.1 - j 4.1

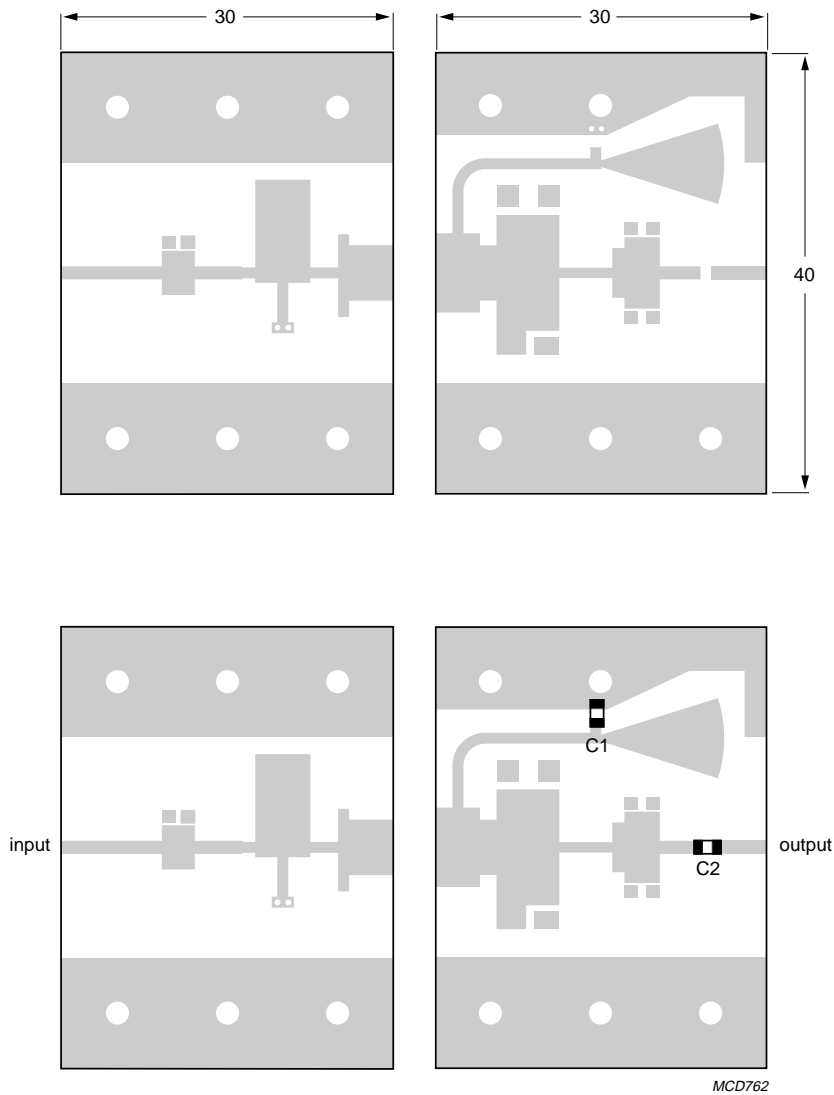
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MCD762

Dimensions in mm.

The components are situated on one side of the copper-clad printed-circuit board with Duroid dielectric ($\epsilon_r = 2.2$), thickness 0.38 mm. The other side is unetched and serves as a ground plane.

C1 = C2 = ATC 100A 5.1 pF

Fig.6 Component layout for 3.1 to 3.5 GHz class-C test circuit.

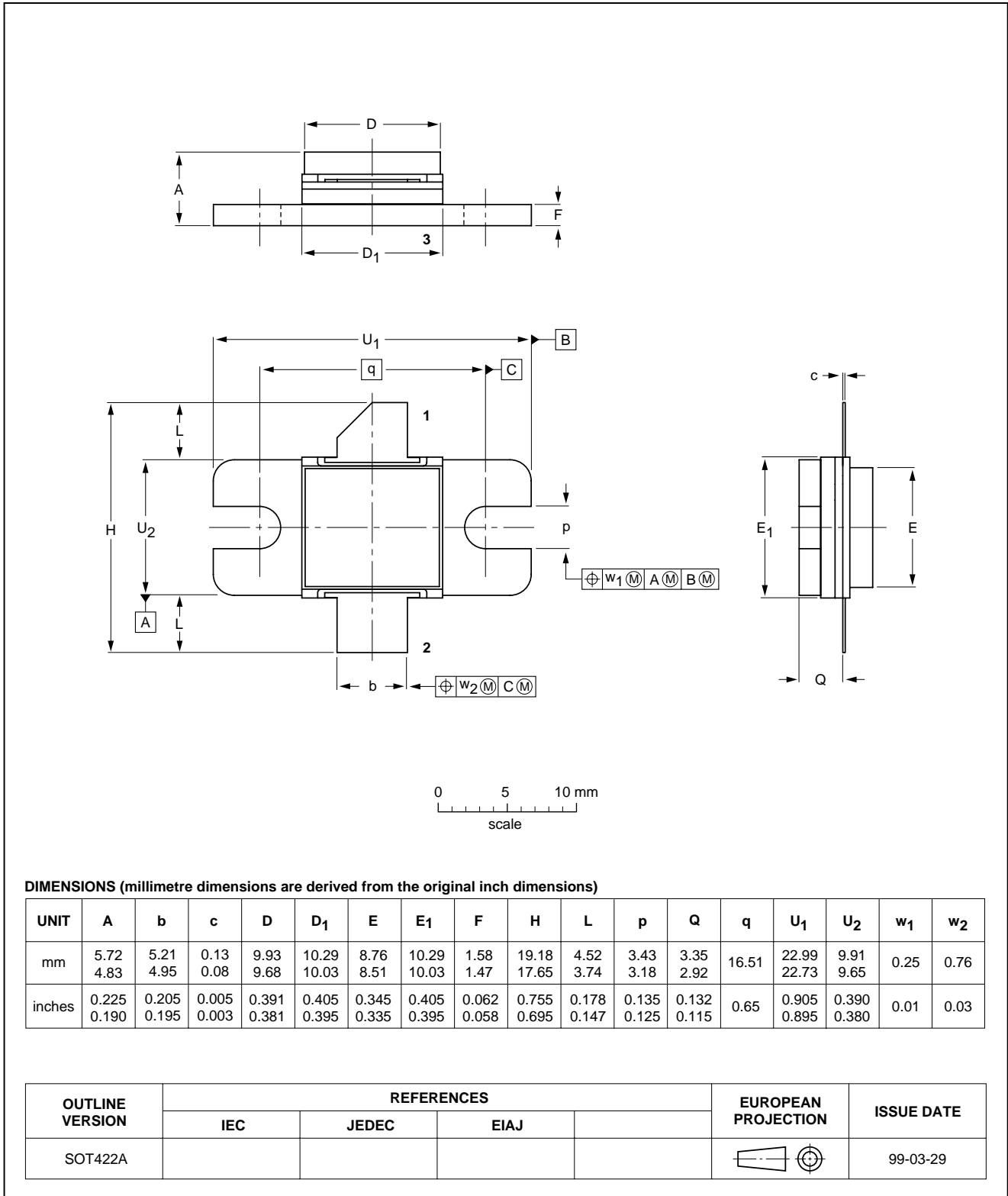
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PACKAGE OUTLINE

Flanged hermetic ceramic package; 2 mounting holes; 2 leads

SOT422A



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DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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Contact information

For additional information please visit <http://www.semiconductors.philips.com>. Fax: +31 40 27 24825

For sales offices addresses send e-mail to: sales.addresses@www.semiconductors.philips.com.

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